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### Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3p250-vqg100t">https://www.e-xfl.com/product-detail/microchip-technology/a3p250-vqg100t</a>

## I/Os Per Package

ProASIC3 Devices	A3P060	A3P125	A3P250		A3P1000	
Package	I/O Type					
	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O <sup>2</sup>	Differential I/O Pairs	Single-Ended I/O <sup>2</sup>	Differential I/O Pairs
VQ100	71	71	68	13	–	–
FG144	96	97	97	24	97	25
FG256	–	–	157	38	177	44
FG484	–	–	–	–	300	74
QNG132	–	84	87	19	–	–

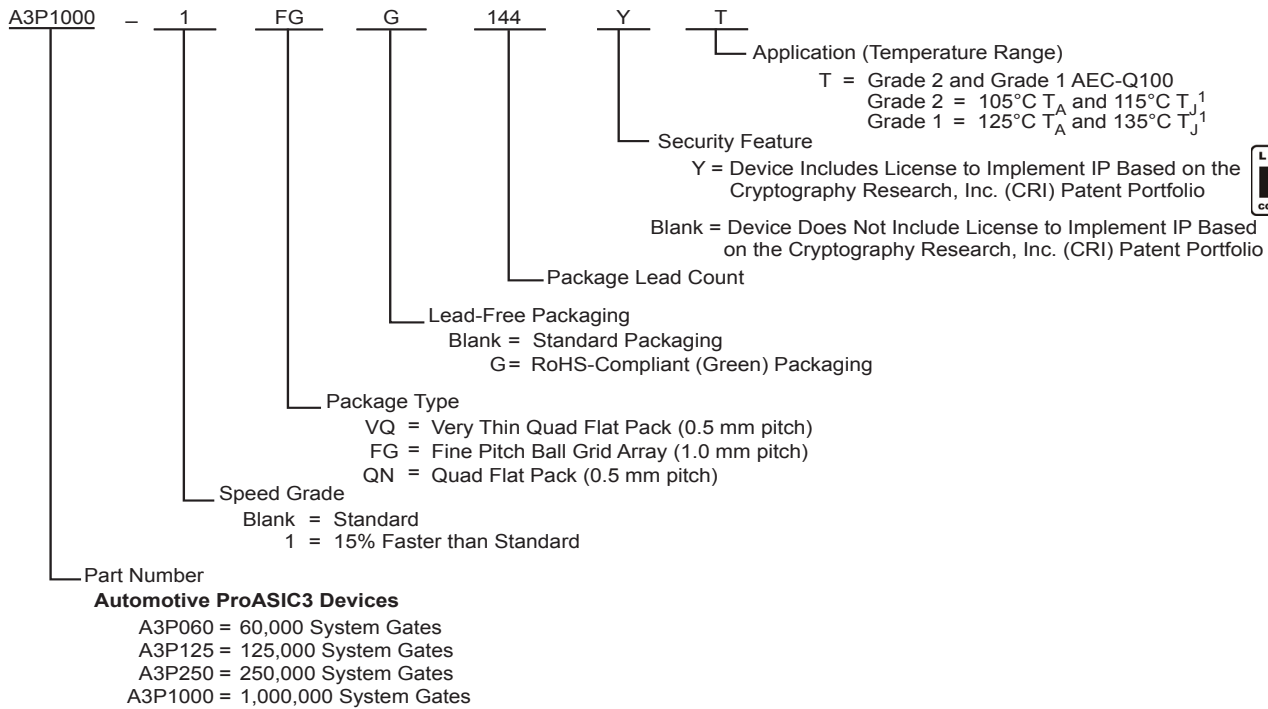
### Notes:

1. When considering migrating your design to a lower- or higher-density device, refer to the [ProASIC3 FPGA Fabric User's Guide](#) to ensure complying with design and board migration requirements.
2. Each used differential I/O pair reduces the number of available single-ended I/Os by two.
3. FG256 and FG484 are footprint-compatible packages.

## Automotive ProASIC3 Device Status

Automotive ProASIC3 Devices	Status
A3P060	Production
A3P125	Production
A3P250	Production
A3P1000	Production

## Automotive ProASIC3 Ordering Information



### Notes:

1.  $T_A$  = Ambient temperature and  $T_J$  = Junction temperature.
2. Minimum order quantities apply. Contact your local Microsemi SoC Products Group sales office for details.

## **User Nonvolatile FlashROM**

Automotive ProASIC3 devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Unique protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, infotainment systems)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard Automotive ProASIC3 IEEE 1532 JTAG programming interface.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

Automotive ProASIC3 development software solutions, Libero<sup>®</sup> System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

## **SRAM**

Automotive ProASIC3 devices have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro.

## **PLL and CCC**

Automotive ProASIC3 devices provide designers with very flexible clock conditioning circuit (CCC) capabilities. Each member of the Automotive ProASIC3 family contains six CCCs. One CCC (center west side) has a PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides. One CCC (center west side) has a PLL.

All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range ( $f_{IN\_CCC}$ ) = 1.5 MHz to 350 MHz
- Output frequency range ( $f_{OUT\_CCC}$ ) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from –7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × 350 MHz /  $f_{OUT\_CCC}$  (for PLL only)

### **Global Clocking**

Automotive ProASIC3 devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

### **I/Os with Advanced I/O Standards**

The Automotive ProASIC3 family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). Automotive ProASIC3 FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

Automotive ProASIC3 banks for the A3P250 and A3P1000 devices support LVPECL, LVDS, B-LVDS, and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

### **Specifying I/O States During Programming**

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the [FlashPro User's Guide](#) for more information.

**Note:** PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify ([Figure 1-4 on page 1-7](#)).

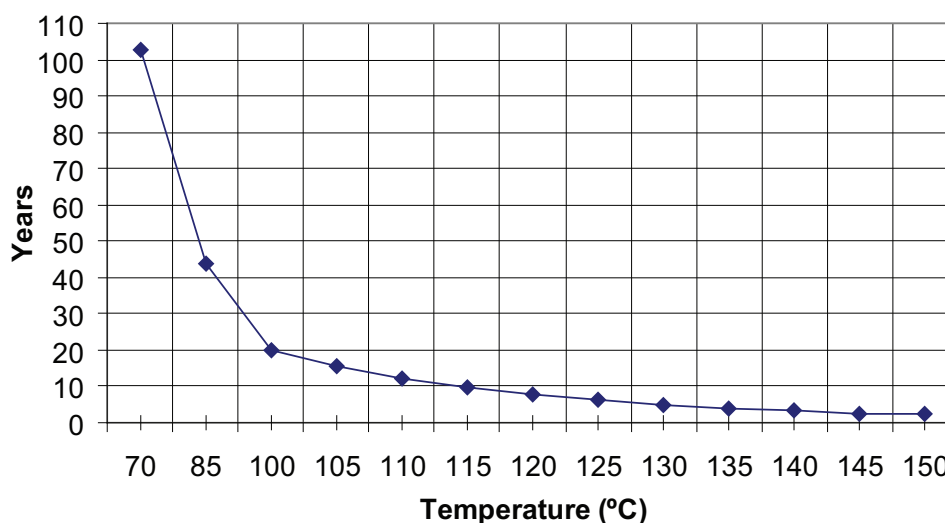
**Table 2-2 • Recommended Operating Conditions**

Symbol	Parameter	Automotive Grade 1	Automotive Grade 2	Units
T <sub>J</sub>	Junction temperature	−40 to +135	−40 to +115	°C
VCC	1.5 V DC core supply voltage	1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage	1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	3.15 to 3.45	3.15 to 3.45	V
	Programming Mode <sup>3</sup> Operation <sup>4</sup>			
VCCPLL	Analog power supply (PLL)	1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV	1.5 V DC supply voltage	1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage	1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage	2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage	3.0 to 3.6	3.0 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O	2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O	3.0 to 3.6	3.0 to 3.6	V

**Notes:**

1. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in [Table 2-14 on page 2-16](#). VMV and VCCI should be at the same voltage within a given I/O bank.
2. All parameters representing voltages are measured with respect to GND unless otherwise specified.
3. The programming temperature range supported is T<sub>ambient</sub> = 0°C to 85°C.
4. V<sub>PUMP</sub> can be left floating during operation (not programming mode).

T <sub>J</sub> (°C)	HTR Lifetime (yrs)
70	102.7
85	43.8
100	20.0
105	15.6
110	12.3
115	9.7
120	7.7
125	6.2
130	5.0
135	4.0
140	3.3
145	2.7
150	2.2



**Note:** HTR time is the period during which you would not expect a verify failure due to flash cell leakage.

**Figure 2-1 • High-Temperature Data Retention (HTR)**

**Table 2-21 • Summary of I/O Timing Characteristics—Software Default Settings**  
**–1 Speed Grade, Automotive-Case Conditions:  $T_J = 115^{\circ}\text{C}$ , Worst Case  $V_{CC} = 1.425\text{ V}$**   
**Worst Case  $V_{CCI} = 3.0\text{ V}$**   
**Standard Plus I/O Banks**

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor	$t_{\text{bOUT}}$	$t_{\text{bP}}$	$t_{\text{bIN}}$	$t_{\text{pY}}$	$t_{\text{EOUT}}$	$t_{\text{ZL}}$	$t_{\text{ZH}}$	$t_{\text{LZ}}$	$t_{\text{HZ}}$	$t_{\text{ZLS}}$	$t_{\text{ZHS}}$	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	High	35 pF	–	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.43	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.55	3.05	0.04	1.23	0.39	3.11	2.99	1.56	1.69	5.23	5.11	ns
1.8 V LVCMOS	8 mA	High	35 pF	–	0.55	3.73	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.99	ns
1.5 V LVCMOS	4 mA	High	35 pF	–	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.18	ns
3.3 V PCI	Per PCI spec	High	10 pF	$25^2$	0.55	2.19	0.04	0.81	0.39	1.27	0.94	2.65	3.06	1.27	0.94	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	$25^2$	0.55	2.19	0.04	0.79	0.39	1.27	0.94	2.65	3.06	1.27	0.94	ns

**Notes:**

1. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.
2. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-48](#) for connectivity. This resistor is not required during normal operation.

**Table 2-41 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew**  
**Automotive-Case Conditions:  $T_J = 115^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
4 mA	STD	0.63	7.79	0.05	1.08	0.45	7.94	6.80	1.22	1.23	7.94	6.80	ns
	-1	0.55	6.85	0.04	0.95	0.39	6.98	5.98	1.26	1.27	6.98	5.98	ns
6 mA	STD	0.63	4.87	0.05	1.08	0.45	4.96	4.13	1.38	1.51	4.96	4.13	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
8 mA	STD	0.63	4.87	0.05	1.08	0.45	4.96	4.13	1.38	1.51	4.96	4.13	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
12 mA	STD	0.63	3.42	0.05	1.08	0.45	1.69	1.38	3.02	3.48	1.69	1.38	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.43	ns
16 mA	STD	0.63	3.42	0.05	1.08	0.45	1.69	1.38	3.02	3.48	1.69	1.38	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.43	ns

**Notes:**

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

**Table 2-42 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Automotive-Case Conditions:  $T_J = 115^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
4 mA	STD	0.63	10.47	0.05	1.08	0.45	10.66	9.11	1.22	1.16	10.66	9.11	ns
	-1	0.55	9.21	0.04	0.95	0.39	9.38	8.01	1.26	1.20	9.38	8.01	ns
6 mA	STD	0.63	7.25	0.05	1.08	0.45	7.38	6.37	1.38	1.44	7.38	6.37	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.60	ns
8 mA	STD	0.63	7.25	0.05	1.08	0.45	7.38	6.37	1.38	1.44	7.38	6.37	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.60	ns
12 mA	STD	0.63	5.46	0.05	1.08	0.45	5.56	4.88	1.49	1.61	5.56	4.88	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.29	ns
16 mA	STD	0.63	5.46	0.05	1.08	0.45	5.56	4.88	1.49	1.61	5.56	4.88	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.29	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.



## Timing Characteristics

**Table 2-46 • 2.5 V LVCMOS High Slew**

Automotive-Case Conditions:  $T_J = 135^{\circ}\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 2.3\text{ V}$   
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	STD	0.64	9.69	0.05	1.45	0.46	8.76	9.69	1.48	1.25	11.26	12.187	ns
	-1	0.55	8.24	0.04	1.23	0.39	7.45	8.24	1.48	1.25	9.58	10.367	ns
6 mA	STD	0.64	5.78	0.05	1.45	0.46	5.63	5.78	1.68	1.62	8.13	8.277	ns
	-1	0.55	4.91	0.04	1.23	0.39	4.79	4.91	1.69	1.63	6.92	7.04	ns
12 mA	STD	0.64	3.98	0.05	1.45	0.46	4.05	3.84	1.82	1.86	6.55	6.338	ns
	-1	0.55	3.39	0.04	1.23	0.39	3.45	3.27	1.83	1.86	5.58	5.392	ns
16 mA	STD	0.64	3.75	0.05	1.45	0.46	1.85	1.69	3.76	3.97	3.06	2.926	ns
	-1	0.55	3.19	0.04	1.23	0.39	1.85	1.69	3.20	3.38	3.06	2.929	ns
24 mA	STD	0.64	3.45	0.05	1.45	0.46	1.70	1.35	3.84	4.47	2.92	2.585	ns
	-1	0.55	2.94	0.04	1.23	0.39	1.71	1.35	3.27	3.80	2.92	2.586	ns

### Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

**Table 2-47 • 2.5 V LVCMOS Low Slew**

Automotive-Case Conditions:  $T_J = 135^{\circ}\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 2.3\text{ V}$   
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	STD	0.64	12.12	0.05	1.45	0.46	12.54	12.74	1.48	1.19	15.04	15.243	ns
	-1	0.55	10.31	0.04	1.23	0.39	10.67	10.84	1.48	1.20	12.80	12.966	ns
6 mA	STD	0.64	8.24	0.05	1.45	0.46	9.07	8.74	1.68	1.57	11.57	11.237	ns
	-1	0.55	7.01	0.04	1.23	0.39	7.71	7.43	1.69	1.57	9.84	9.559	ns
12 mA	STD	0.64	6.91	0.05	1.45	0.46	7.04	6.62	1.82	1.80	9.54	9.117	ns
	-1	0.55	5.88	0.04	1.23	0.39	5.99	5.63	1.83	1.80	8.11	7.756	ns
16 mA	STD	0.64	6.44	0.05	1.45	0.46	6.56	6.18	1.86	1.86	9.06	8.678	ns
	-1	0.55	5.48	0.04	1.23	0.39	5.58	5.26	1.86	1.86	7.71	7.382	ns
24 mA	STD	0.64	6.16	0.05	1.45	0.46	6.15	6.16	1.90	2.10	8.65	8.657	ns
	-1	0.55	5.24	0.04	1.23	0.39	5.23	5.24	1.90	2.10	7.36	7.364	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

**Table 2-70 • 1.5 V LVCMOS High Slew**

Automotive-Case Conditions:  $T_J = 135^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V  
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{\text{DOUT}}$	$t_{\text{DP}}$	$t_{\text{DIN}}$	$t_{\text{PY}}$	$t_{\text{EOUT}}$	$t_{\text{ZL}}$	$t_{\text{ZH}}$	$t_{\text{LZ}}$	$t_{\text{HZ}}$	$t_{\text{ZLS}}$	$t_{\text{ZHS}}$	Units
2 mA	STD	0.64	8.76	0.05	1.59	0.46	7.63	9.35	1.87	1.50	10.13	11.851	ns
	-1	0.55	7.45	0.04	1.35	0.39	6.49	7.95	1.87	1.50	8.62	10.081	ns
4 mA	STD	0.64	5.41	0.05	1.59	0.46	5.42	5.94	2.07	1.84	7.92	8.442	ns
	-1	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.181	ns

**Notes:**

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

**Table 2-71 • 1.5 V LVCMOS Low Slew**

Automotive-Case Conditions:  $T_J = 135^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V  
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	$t_{\text{DOUT}}$	$t_{\text{DP}}$	$t_{\text{DIN}}$	$t_{\text{PY}}$	$t_{\text{EOUT}}$	$t_{\text{ZL}}$	$t_{\text{ZH}}$	$t_{\text{LZ}}$	$t_{\text{HZ}}$	$t_{\text{ZLS}}$	$t_{\text{ZHS}}$	Units
2 mA	STD	0.64	13.51	0.05	1.45	0.46	14.32	14.29	1.88	1.43	16.82	16.794	ns
	-1	0.55	11.49	0.04	1.23	0.39	12.18	12.16	1.88	1.43	14.31	14.286	ns
4 mA	STD	0.64	10.38	0.05	1.45	0.46	11.40	10.67	2.07	1.77	13.90	13.175	ns
	-1	0.55	8.83	0.04	1.23	0.39	9.70	9.08	2.07	1.77	11.82	11.207	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

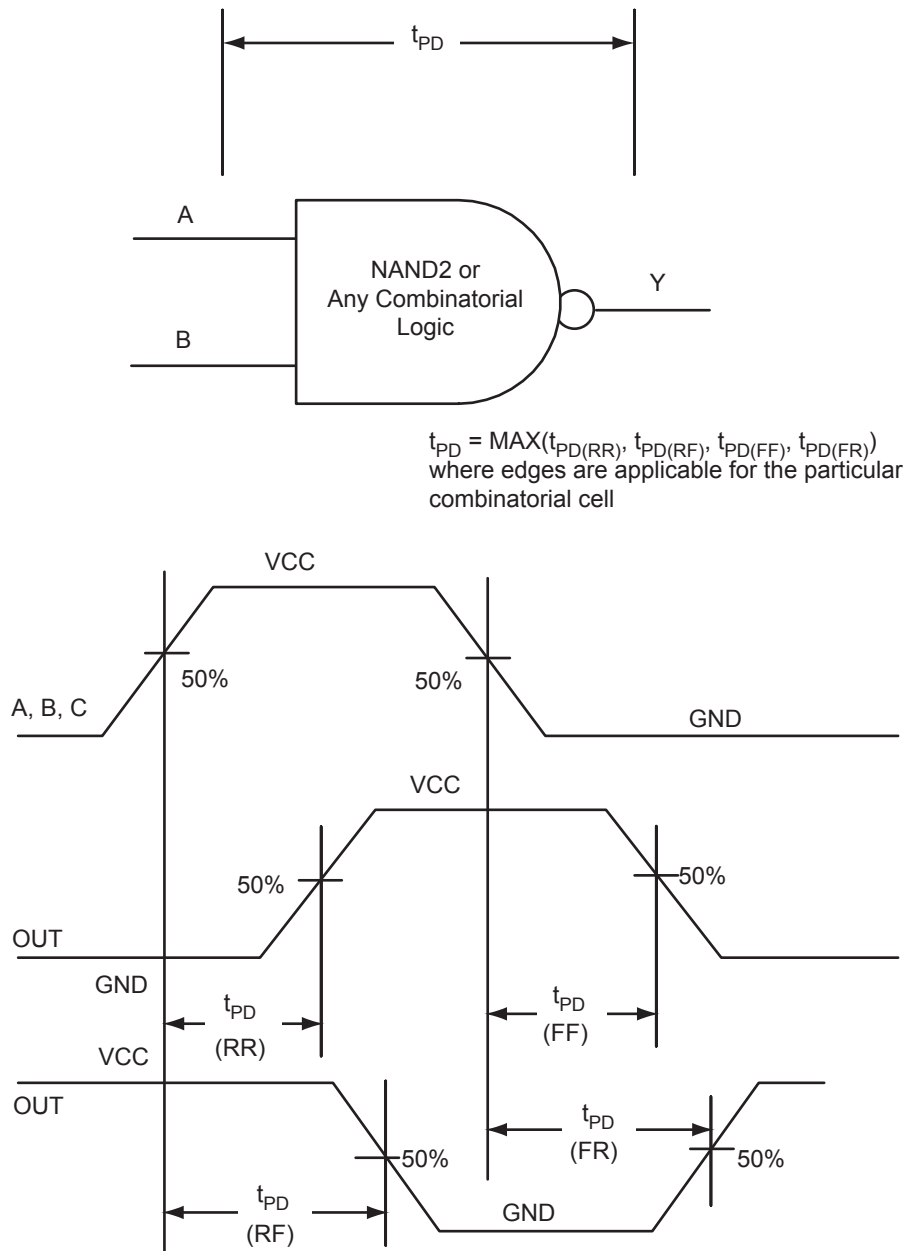
**Table 2-72 • 1.5 V LVCMOS High Slew**

Automotive-Case Conditions:  $T_J = 115^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V  
Applicable to Advanced I/O Banks

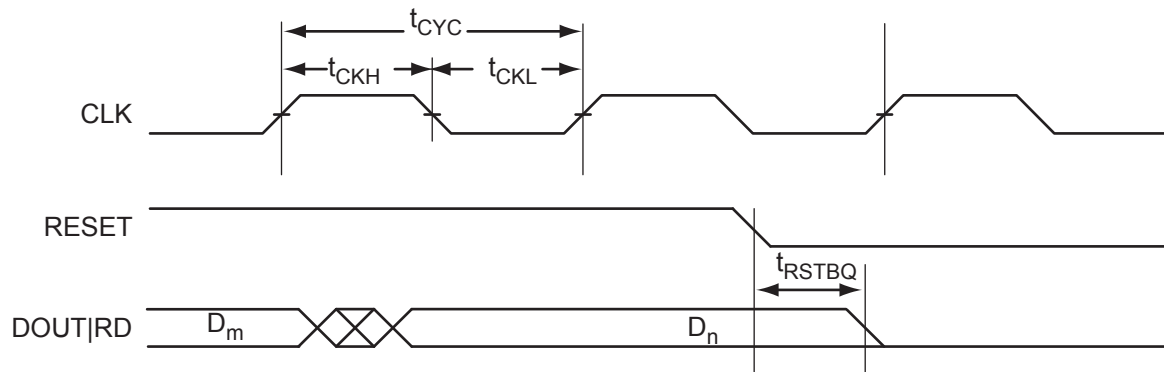
Drive Strength	Speed Grade	$t_{\text{DOUT}}$	$t_{\text{DP}}$	$t_{\text{DIN}}$	$t_{\text{PY}}$	$t_{\text{EOUT}}$	$t_{\text{ZL}}$	$t_{\text{ZH}}$	$t_{\text{LZ}}$	$t_{\text{HZ}}$	$t_{\text{ZLS}}$	$t_{\text{ZHS}}$	Units
2 mA	STD	0.63	9.05	0.05	1.56	0.45	7.38	9.05	1.81	1.45	9.80	11.47	ns
	-1	0.53	7.70	0.04	1.32	0.38	6.28	7.70	1.81	1.45	8.34	9.75	ns
4 mA	STD	0.63	5.75	0.05	1.56	0.45	5.25	5.75	2.00	1.78	7.67	8.17	ns
	-1	0.53	4.89	0.04	1.32	0.38	4.46	4.89	2.00	1.78	6.52	6.95	ns
6 mA	STD	0.63	5.05	0.05	1.56	0.45	4.92	5.05	2.04	1.87	7.34	7.47	ns
	-1	0.53	4.29	0.04	1.32	0.38	4.19	4.29	2.04	1.87	6.24	6.35	ns
8 mA	STD	0.63	4.41	0.05	1.56	0.45	2.18	1.91	4.27	4.55	3.35	3.11	ns
	-1	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns
12 mA	STD	0.63	4.41	0.05	1.56	0.45	2.18	1.91	4.27	4.55	3.35	3.11	ns
	-1	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns

**Notes:**

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.



**Figure 2-25 • Timing Model and Waveforms**



**Figure 2-35 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18**

## Timing Characteristics

**Table 2-121 • FIFO**
**Worst-Case Automotive Conditions:  $T_J = 135^{\circ}\text{C}$ ,  $V_{CC} = 1.425\text{ V}$** 

Parameter	Description	–1	Std.	Units
$t_{\text{ENS}}$	REN, WEN Setup Time	1.97	1.67	ns
$t_{\text{ENH}}$	REN, WEN Hold Time	0.03	0.02	ns
$t_{\text{BKS}}$	BLK Setup Time	0.28	0.32	ns
$t_{\text{BKH}}$	BLK Hold Time	0.00	0.00	ns
$t_{\text{DS}}$	Input Data (WD) Setup Time	0.26	0.22	ns
$t_{\text{DH}}$	Input Data (WD) Hold Time	0.00	0.00	ns
$t_{\text{CKQ1}}$	Clock High to New Data Valid on RD (flow-through)	3.37	2.86	ns
$t_{\text{CKQ2}}$	Clock High to New Data Valid on RD (pipelined)	1.28	1.09	ns
$t_{\text{RCKEF}}$	RCLK High to Empty Flag Valid	2.45	2.09	ns
$t_{\text{WCKFF}}$	WCLK High to Full Flag Valid	2.33	1.98	ns
$t_{\text{CKAF}}$	Clock High to Almost Empty/Full Flag Valid	8.85	7.53	ns
$t_{\text{RSTFG}}$	RESET Low to Empty/Full Flag Valid	2.42	2.06	ns
$t_{\text{RSTAF}}$	RESET Low to Almost Empty/Full Flag Valid	8.76	7.45	ns
$t_{\text{RSTBQ}}$	RESET Low to Data Out Low on RD (flow-through)	1.32	1.12	ns
	RESET Low to Data Out Low on RD (pipelined)	1.32	1.12	ns
$t_{\text{REMRSTB}}$	RESET Removal	0.41	0.35	ns
$t_{\text{RECRSTB}}$	RESET Recovery	2.14	1.82	ns
$t_{\text{MPWRSTB}}$	RESET Minimum Pulse Width	0.30	0.26	ns
$t_{\text{CYC}}$	Clock Cycle Time	4.62	3.93	ns
$F_{\text{MAX}}$	Maximum Frequency for FIFO	217	255	MHz

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

#### **VPUMP** **Programming Supply Voltage**

Automotive ProASIC3 devices support single-voltage ISP of the configuration flash and FlashROM. For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in the datasheet.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01  $\mu$ F and 0.33  $\mu$ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

## **User Pins**

### **I/O** **User Input/Output**

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

### **GL** **Globals**

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the [Automotive ProASIC3 FPGA Fabric User's Guide](#). All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the "I/O Structures in IGLOO and ProASIC3 Devices" chapter of the [Automotive ProASIC3 FPGA Fabric User's Guide](#) for an explanation of the naming of global pins.

QN132	
Pin Number	A3P250 Function
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG144	
Pin Number	A3P060 Function
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ



FG144	
Pin Number	A3P250 Function
K1	GEB0/IO99NDB3
K2	GEA1/IO98PDB3
K3	GEA0/IO98NDB3
K4	GEA2/IO97RSB2
K5	IO90RSB2
K6	IO84RSB2
K7	GND
K8	IO66RSB2
K9	GDC2/IO63RSB2
K10	GND
K11	GDA0/IO60VDB1
K12	GDB0/IO59VDB1
L1	GND
L2	VMV3
L3	GEB2/IO96RSB2
L4	IO91RSB2
L5	VCCIB2
L6	IO82RSB2
L7	IO80RSB2
L8	IO72RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO95RSB2
M3	IO92RSB2
M4	IO89RSB2
M5	IO87RSB2
M6	IO85RSB2
M7	IO78RSB2
M8	IO76RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	A3P1000 Function
K1	GEB0/IO189NDB3
K2	GEA1/IO188PDB3
K3	GEA0/IO188NDB3
K4	GEA2/IO187RSB2
K5	IO169RSB2
K6	IO152RSB2
K7	GND
K8	IO117RSB2
K9	GDC2/IO116RSB2
K10	GND
K11	GDA0/IO113NDB1
K12	GDB0/IO112NDB1
L1	GND
L2	VMV3
L3	GEB2/IO186RSB2
L4	IO172RSB2
L5	VCCIB2
L6	IO153RSB2
L7	IO144RSB2
L8	IO140RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO185RSB2
M3	IO173RSB2
M4	IO168RSB2
M5	IO161RSB2
M6	IO156RSB2
M7	IO145RSB2
M8	IO141RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG484		FG484		FG484	
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
A1	GND	B15	IO63RSB0	D7	GAB0/IO02RSB0
A2	GND	B16	IO66RSB0	D8	IO16RSB0
A3	VCCIB0	B17	IO68RSB0	D9	IO22RSB0
A4	IO07RSB0	B18	IO70RSB0	D10	IO28RSB0
A5	IO09RSB0	B19	NC	D11	IO35RSB0
A6	IO13RSB0	B20	NC	D12	IO45RSB0
A7	IO18RSB0	B21	VCCIB1	D13	IO50RSB0
A8	IO20RSB0	B22	GND	D14	IO55RSB0
A9	IO26RSB0	C1	VCCIB3	D15	IO61RSB0
A10	IO32RSB0	C2	IO220PDB3	D16	GBB1/IO75RSB0
A11	IO40RSB0	C3	NC	D17	GBA0/IO76RSB0
A12	IO41RSB0	C4	NC	D18	GBA1/IO77RSB0
A13	IO53RSB0	C5	GND	D19	GND
A14	IO59RSB0	C6	IO10RSB0	D20	NC
A15	IO64RSB0	C7	IO14RSB0	D21	NC
A16	IO65RSB0	C8	VCC	D22	NC
A17	IO67RSB0	C9	V <sub>CC</sub>	E1	IO219NDB3
A18	IO69RSB0	C10	IO30RSB0	E2	NC
A19	NC	C11	IO37RSB0	E3	GND
A20	VCCIB0	C12	IO43RSB0	E4	GAB2/IO224PDB3
A21	GND	C13	NC	E5	GAA2/IO225PDB3
A22	GND	C14	VCC	E6	GNDQ
B1	GND	C15	VCC	E7	GAB1/IO03RSB0
B2	VCCIB3	C16	NC	E8	IO17RSB0
B3	NC	C17	NC	E9	IO21RSB0
B4	IO06RSB0	C18	GND	E10	IO27RSB0
B5	IO08RSB0	C19	NC	E11	IO34RSB0
B6	IO12RSB0	C20	NC	E12	IO44RSB0
B7	IO15RSB0	C21	NC	E13	IO51RSB0
B8	IO19RSB0	C22	VCCIB1	E14	IO57RSB0
B9	IO24RSB0	D1	IO219PDB3	E15	GBC1/IO73RSB0
B10	IO31RSB0	D2	IO220NDB3	E16	GBB0/IO74RSB0
B11	IO39RSB0	D3	NC	E17	IO71RSB0
B12	IO48RSB0	D4	GND	E18	GBA2/IO78PDB1
B13	IO54RSB0	D5	GAA0/IO00RSB0	E19	IO81PDB1
B14	IO58RSB0	D6	GAA1/IO01RSB0	E20	GND

## 5 – Datasheet Information

### List of Changes

The following table lists critical changes that were made in each revision of the Automotive ProASIC3 datasheet.

Revision	Changes	Page
Revision 5 (January 2013)	The "Automotive ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43222).	1-III
	Added a note to Table 2-2 • Recommended Operating Conditions (SAR 43675): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to $85^{\circ}\text{C}$ .	2-2
	The note in Table 2-116 • Automotive ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42560).	2-80
	Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 4 (September 2012)	The "Specifying I/O States During Programming" section is new (SAR 34691).	1-6
	Table 2-2 • Recommended Operating Conditions was revised to change VPUMP values for programming mode from "3.0 to 3.6" to "3.15 to 3.45" (SAR 34703).	2-2
	Maximum values for VIL and VIH were corrected in LVPECL Table 2-86 • Minimum and Maximum DC Input and Output Levels (SAR 37693).	2-52
	Values were added for $F_{\text{DDRIMAX}}$ and $F_{\text{DDOMAX}}$ in the following tables (SAR 34804): Table 2-99 • Input DDR Propagation Delays ( $T_J = 135^{\circ}\text{C}$ ) Table 2-100 • Input DDR Propagation Delays ( $T_J = 115^{\circ}\text{C}$ ) Table 2-102 • Output DDR Propagation Delays ( $T_J = 135^{\circ}\text{C}$ ) Table 2-103 • Output DDR Propagation Delays ( $T_J = 115^{\circ}\text{C}$ )	2-64 to 2-68
	Added values for minimum pulse width and removed the FRMAX row from Table 2-108 through Table 2-115 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SAR 36966).	2-76
	SRAM collision data was added to Table 2-117 • RAM4K9 through Table 2-120 • RAM512X18. Maximum frequency, $F_{\text{MAX}}$ , was updated in Table 2-118 • RAM512X18 (SAR 40859).	2-86 to 2-89
	The "VMVx I/O Supply Voltage (quiet)" section was revised. The sentence, "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" was replaced with, "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38323). VMV pins must be connected to the corresponding VCCI pins, as noted in the "VMVx I/O Supply Voltage (quiet)" section, for an ESD enhancement.	3-1
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40266).	N/A
Revision 3 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1

Revision	Changes	Page
Revision 2 (May 2012)	The "Extended Temperature AEC-Q100–Qualified Devices" section was modified to include the low end of the temperature range, –40°C, for Grade 1 and Grade 2 AEC-Q100 qualified devices (SAR 34915).	I
	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34674).	I, 1-1
	The Y security option and Licensed DPA Logo were added to the "Automotive ProASIC3 Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34719).	III
	A note defining $T_A$ and $T_J$ was added to the "Automotive ProASIC3 Ordering Information" section (SAR 37547).	III
	The following sentence was deleted from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of Automotive ProASIC3 devices via an IEEE 1532 JTAG interface" (SAR 34682).	1-3
	In Table 2-2 • Recommended Operating Conditions, VCCPLL analog power supply (PLL) was changed from "1.4 to 1.6" to "1.425 to 1.575" (SAR 34718).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—PCLOCK" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the <i>Automotive ProASIC3 FPGA Fabric User's Guide</i> (SAR 34738).	2-10
	$t_{DOUT}$ was corrected to $t_{DIN}$ in Figure 2-4 • Input Buffer Timing Model and Delays (example) (SAR 37111).	2-13
	The equations in the notes for Table 2-27 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34754).	2-23
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34882).	2-27
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 34795): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-33
	The table notes for Table 2-82 • Minimum and Maximum DC Input and Output Levels were not necessary and were removed (SAR 34811).	2-50
	The following figures were deleted (SAR 29991). Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 34861). Figure 2-35 • Write Access after Write to Same Address Figure 2-36 • Read Access after Write to Same Address Figure 2-35 • Read Access after Write to Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-39 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35744).	2-83, 2-86, 2-92, 2-94
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 34838).	2-91
	Table 2-116 • Automotive ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34822).	2-80